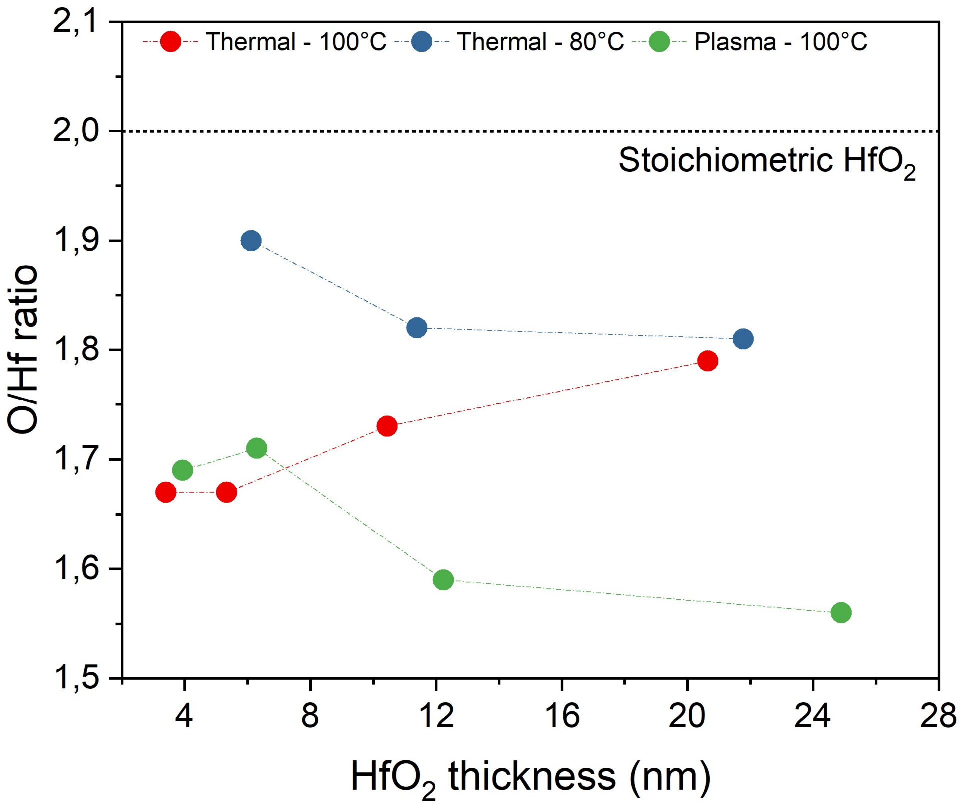

Figure 1 – Stoichiometry of ALD grown HfO2 films depending on the growth process and thickness.

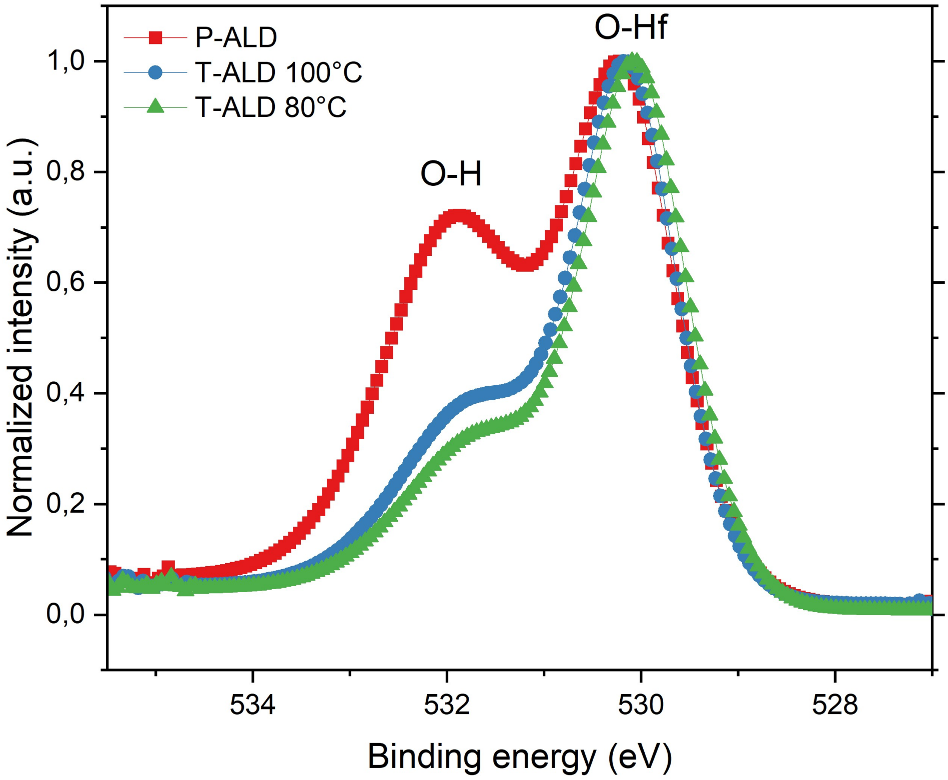

Figure 2 – XPS O (1s) region of HfO2 films with similar thickness grown from different ALD process. A major change in the OH contribution is evident.